

AON1611

20V P-Channel MOSFET

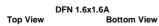
General Description

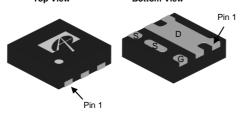
The AON1611 combines advanced trench MOSFET technology with a low resistance package to provide extremely low $R_{\text{DS(ON)}}$. This device is ideal for load switch and battery protection applications.

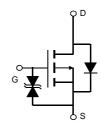
Product Summary

Typical ESD protection HBM Class 2









Absolute Maximum Ratings T_A=25℃ unless otherwise noted

Parameter Symbol Maximum	Units
Drain-Source Voltage V _{DS} -20	V
Gate-Source Voltage V _{GS} ±8	V
Continuous Drain T _A =25℃ -4	
Current ^G T _A =70℃ ^{1D} -3	A
Pulsed Drain Current ^c I _{DM} -16	
T _A =25°C P _D 1.8	W
Power Dissipation ^A T _A =70℃ TD 1.15	VV
Junction and Storage Temperature Range T _J , T _{STG} -55 to 150	C

Thermal Characteristics							
Parameter		Symbol	Тур	Max	Units		
Maximum Junction-to-Ambient A	t ≤ 10s	В	56	70	C/W		
Maximum Junction-to-Ambient AD	Steady-State	$\kappa_{\theta JA}$	88	110	C/W		



Electrical Characteristics (T_J=25℃ unless otherwise noted)

Symbol	Parameter	Conditions	Min	Тур	Max	Units
STATIC I	PARAMETERS					
BV _{DSS}	Drain-Source Breakdown Voltage	$I_D = -250 \mu A, V_{GS} = 0 V$	-20			V
I _{DSS}	Zero Gate Voltage Drain Current	V _{DS} =-20V, V _{GS} =0V			-1	μΑ
		T _J =55℃			-5	
I _{GSS}	Gate-Body leakage current	V_{DS} =0V, V_{GS} =±8V			±10	μΑ
$V_{GS(th)}$	Gate Threshold Voltage	$V_{DS}=V_{GS}$, $I_{D}=-250\mu A$	-0.3	-0.6	-0.9	V
$I_{D(ON)}$	On state drain current	V_{GS} =-10V, V_{DS} =-5V	-16			Α
R _{DS(ON)}		V _{GS} =-4.5V, I _D =-4A		46	58	mΩ
		T _J =125℃		64.5	80	11152
	Static Drain-Source On-Resistance	V_{GS} =-2.5V, I_D =-3A		58	76	$m\Omega$
		V_{GS} =-1.8V, I_D =-2A		74	98	$m\Omega$
		V_{GS} =-1.5V, I_D =-1A		88	120	$m\Omega$
g _{FS}	Forward Transconductance	V_{DS} =-5V, I_{D} =-4A		15		S
V_{SD}	Diode Forward Voltage	I_S =-1A, V_{GS} =0V		-0.66	-1	V
Is	Maximum Body-Diode Continuous Current				-2.5	Α
DYNAMIC	CPARAMETERS					
C _{iss}	Input Capacitance			550		pF
C _{oss}	Output Capacitance	V_{GS} =0V, V_{DS} =-10V, f=1MHz		93		pF
C _{rss}	Reverse Transfer Capacitance			64		pF
R_g	Gate resistance	V_{GS} =0V, V_{DS} =0V, f=1MHz		12		Ω
SWITCH	NG PARAMETERS					
Q _g (4.5V)	Total Gate Charge			7	10	nC
Q_{gs}	Gate Source Charge	V_{GS} =-4.5V, V_{DS} =-10V, I_{D} =-4A		1		nC
Q_{gd}	Gate Drain Charge			1.8		nC
t _{D(on)}	Turn-On DelayTime			15		ns
t _r	Turn-On Rise Time	V_{GS} =-4.5V, V_{DS} =-10V, R_L =2.5 Ω ,		33		ns
t _{D(off)}	Turn-Off DelayTime	$R_{GEN}=3\Omega$		50		ns
t _f	Turn-Off Fall Time]		43		ns
t _{rr}	Body Diode Reverse Recovery Time	I _F =-4A, dI/dt=100A/μs		16		ns
Q_{rr}	Body Diode Reverse Recovery Charge	I _F =-4A, dI/dt=100A/μs		6.5		nC

A. The value of $R_{\theta JA}$ is measured with the device mounted on 1in^2 FR-4 board with 2oz. Copper, in a still air environment with T_{A} =25° C. The Power dissipation P_{DSM} is based on $R_{\theta JA}$ t \leqslant 10s value and the maximum allowed junction temperature of 150° C. The value in any given application depends on the user's specific board design.

THIS PRODUCT HAS BEEN DESIGNED AND QUALIFIED FOR THE CONSUMER MARKET. APPLICATIONS OR USES AS CRITICAL COMPONENTS IN LIFE SUPPORT DEVICES OR SYSTEMS ARE NOT AUTHORIZED. AOS DOES NOT ASSUME ANY LIABILITY ARISING OUT OF SUCH APPLICATIONS OR USES OF ITS PRODUCTS. AOS RESERVES THE RIGHT TO IMPROVE PRODUCT DESIGN, FUNCTIONS AND RELIABILITY WITHOUT NOTICE.

B. The power dissipation P_D is based on $T_{J(MAX)}$ =150 ° C, using junction-to-case thermal resistance, and is more useful in setting the upper dissipation limit for cases where additional heatsinking is used.

C. Repetitive rating, pulse width limited by junction temperature T_{J(MAX)}=150° C. Ratings are based on low frequency and duty cycles to keep initial $T_J = 25^{\circ}$ C.

D. The $R_{\theta JA}$ is the sum of the thermal impedance from junction to case $R_{\theta JC}$ and case to ambient.

E. The static characteristics in Figures 1 to 6 are obtained using <300µs pulses, duty cycle 0.5% max.

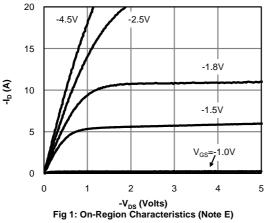
F. These curves are based on the junction-to-case thermal impedance which is measured with the device mounted to a large heatsink, assuming a maximum junction temperature of T_{J(MAX)}=150° C. The SOA curve provides a single pulse rating.

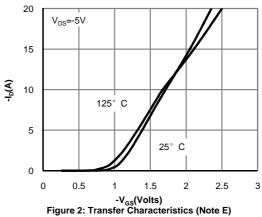
G. The maximum current rating is package limited.

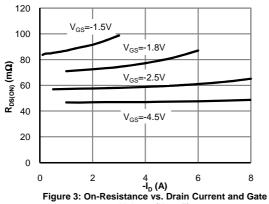
H. These tests are performed with the device mounted on 1 in FR-4 board with 2oz. Copper, in a still air environment with $T_A=25^{\circ}$ C.



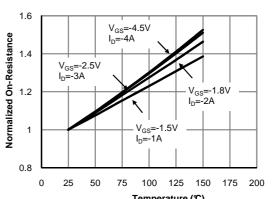
TYPICAL ELECTRICAL AND THERMAL CHARACTERISTICS



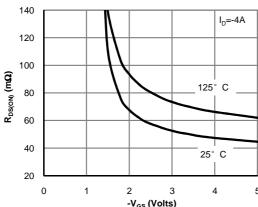




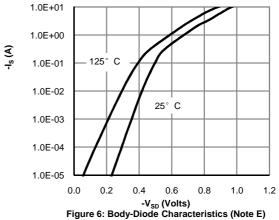
Voltage (Note E)



Temperature (°C)
Figure 4: On-Resistance vs. Junction Temperature
(Note E)

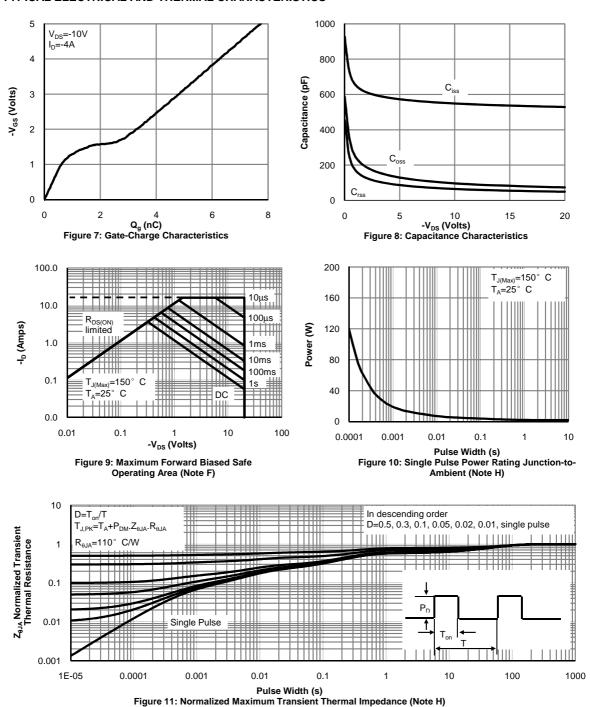


-V_{GS} (Volts)
Figure 5: On-Resistance vs. Gate-Source Voltage (Note E)



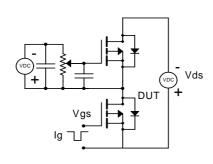


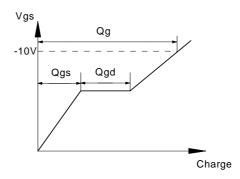
TYPICAL ELECTRICAL AND THERMAL CHARACTERISTICS



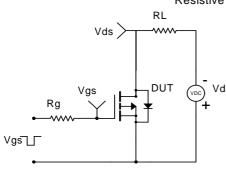


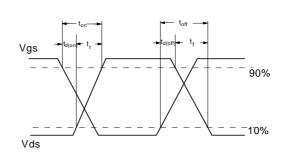
Gate Charge Test Circuit & Waveform



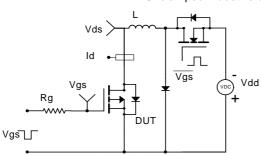


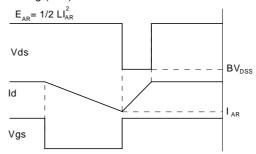
Resistive Switching Test Circuit & Waveforms



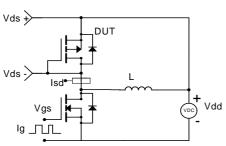


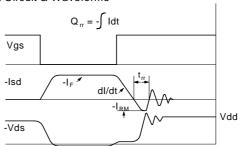
Unclamped Inductive Switching (UIS) Test Circuit & Waveforms





Diode Recovery Test Circuit & Waveforms





X-ON Electronics

Largest Supplier of Electrical and Electronic Components

Click to view similar products for alpha & omega manufacturer:

Other Similar products are found below:

AOT1608L AO4492 AOD478 AOD468 AOZ6135HI AO5404E AOD482 AO3402 AOTF10B60D AOU3N50 AOZ1235QI-01

AOK42S60L AON7534 AOD3N50 AO4468 AO3401A AO3415 AON2403 AOD4130 AOB290L AOTF42S60L AOTF190A60L

AO4404B AON6756 AO4813 AO3414 aot412 AO4818 AOT270AL AO6420 AO3442 AOT2918L AO4616 AO4294 AOZ1020AI

AON6250 AON6444 AOZ3011PI AO8820 AOT10N65 AOK20S60L AOK20N60L AON6548 AO3415A AOT470 AOZ8905CI

AOK60N30L AOT410L AON6280 AON6414A